

2A, 200V-1000V High Efficient Recovery Surface Mount Rectifier

FEATURES

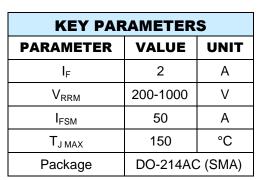
- · Glass passivated junction chip
- Ideal for automated placement
- Low reverse leakage
- Moisture sensitivity level: level 1, per J-STD-020
- Compliant to RoHS directive 2011/65/EU and in accordance to WEEE 2002/96/EC
- Halogen-free according to IEC 61249-2-21

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- Switch Mode Power Supply
- Inverters and Converters
- Free Wheeling diodes

MECHANICAL DATA

- Case: DO-214AC (SMA)
- Molding compound meets UL 94V-0 flammability rating
- Terminal: Matte tin plated leads, solderable per J-STD-002
- Meet JESD 201 class 1 whisker test
- · Polarity: Indicated by cathode band
- Weight: 0.06 g (approximately)











DO-214AC (SMA)



ABSOLUTE MAXIMUM RATINGS (T _A = 25°C unless otherwise noted)								
PARAMETER		SYMBOL	HS2DA -T	HS2GA -T	HS2JA -T	HS2KA -T	HS2MA -T	UNIT
Marking code on the dev	vice .		HS2DA	HS2GA	HS2JA	HS2KA	HS2MA	
Repetitive peak reverse	voltage	V_{RRM}	200	400	600	800	1000	V
Reverse voltage, total rms value		V _{R(RMS)}	140	280	420	560	700	V
DC blocking voltage		V_{DC}	200	400	600	800	1000	V
Forward current		I _F	2				Α	
Surge peak forward current single half sine-	8.3 ms at T _A = 25°C	I			50			А
wave superimposed on rated load per diode $1.0 \text{ ms at } T_A = 25^{\circ}\text{C}$		I _{FSM}			124			Α
Junction temperature		T _J	-55 to +150			°C		
Storage temperature		T _{STG}	-55 to +150				°C	

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THERMAL PERFORMANCE				
PARAMETER	SYMBOL	TYP	UNIT	
Junction-to-lead thermal resistance per diode	R _{OJL}	14	°C/W	
Junction-to-ambient thermal resistance per diode	R _{OJA}	86	°C/W	
Junction-to-case thermal resistance per diode	R _{eJC}	23	°C/W	

Thermal Performance Note: Units mounted on PCB (5mm x 5mm Cu pad test board)

PARAMETER		CONDITIONS	SYMBOL	TYP	MAX	UNIT
	HS2DA-T	I _F = 1A, T _J = 25°C		0.84	-	V
		I _F = 2A, T _J = 25°C		0.91	1.0	V
		I _F = 1A, T _J = 125°C		0.69	-	V V V V V V V V V V V V V V V V V V V
		I _F = 2A, T _J = 125°C		0.78	0.91	V
		I _F = 1A, T _J = 25°C		0.93	- 1 4	V
Forward voltage per diode (1)	HS2GA-T	I _F = 2A, T _J = 25°C	V	1.03 1.4 0.77 -	V	
roiward voltage per diode	H32GA-1	I _F = 1A, T _J = 125°C	V_{F}	0.77	-	V
		I _F = 2A, T _J = 125°C]	0.88	0.99	V
		I _F = 1A, T _J = 25°C		1.25	-	V
	HS2JA-T to HS2MA-T	I _F = 2A, T _J = 25°C		1.40	1.7	99 V V V V V V V V V V V V V V V V V V
	HSZJA-1 (U HSZWA-1	I _F = 1A, T _J = 125°C		1.00	-	
		I _F = 2A, T _J = 125°C		1.16	1.41	V
Reverse current @ rated V _R per diode ⁽²⁾		T _J = 25°C		-	5	μΑ
Reverse current & rated V _R p	er diode	T _J = 125°C	I _R	-	100	μA
Davaraa raaayaru tima	HS2DA-T to HS2GA-T	I _F =0.5A,I _R =1.0A,	t _{rr}	-	50	ns
Reverse recovery time	HS2JA-T to HS2MA-T	Irr=0.25A		-	75	ns
	HS2DA-T		CJ	12	-	pF
Junction capacitance per diode	HS2GA-T	1 MHz, V _R =4.0V		20	-	pF
	HS2JA-T to HS2MA-T			26	-	pF

Notes:

- (1) Pulse test with PW=0.3 ms
- (2) Pulse test with PW=30 ms

ORDERING INFORMATION					
ORDERING CODE	PACKAGE	PACKING			
HS2XA-T R3G ⁽¹⁾	SMA	1,800 / 7" Plastic reel			
HS2XA-T M2G ⁽¹⁾	SMA	7,500 / 13" Plastic reel			
HS2XA-T R2G ⁽¹⁾	SMA	7,500 / 13" Paper reel			

Notes:

(1) "X" defines voltage from 200V(HS2DA-T) to 1000V(HS2MA-T)



CHARACTERISTICS CURVES

 $(T_A = 25^{\circ}C \text{ unless otherwise noted})$

Fig.1 Forward Current Derating Curve

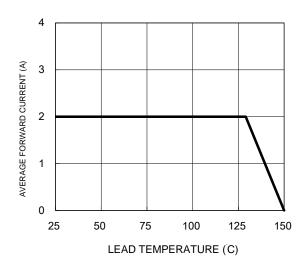


Fig.3 Typical Reverse Characteristics

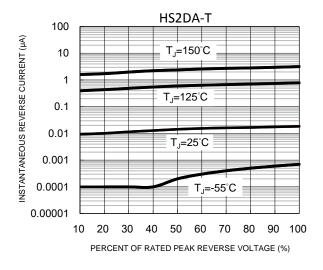


Fig.5 Typical Reverse Characteristics

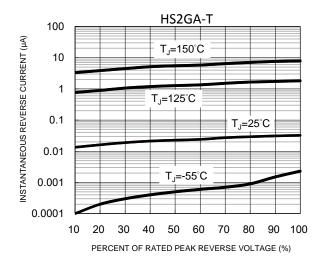


Fig.2 Typical Junction Capacitance

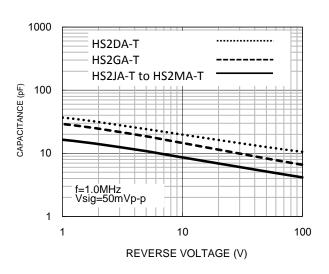


Fig.4 Typical Forward Characteristics

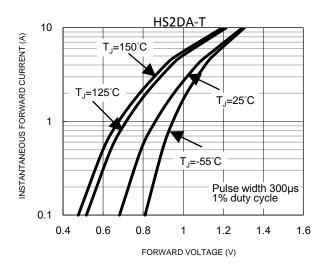
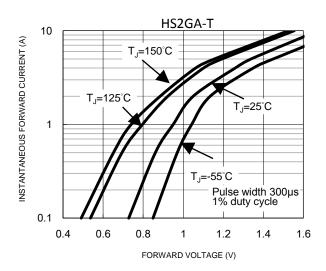


Fig.6 Typical Forward Characteristics



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Fig.7 Typical Reverse Characteristics

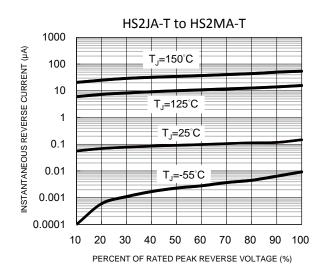


Fig.8 Typical Forward Characteristics

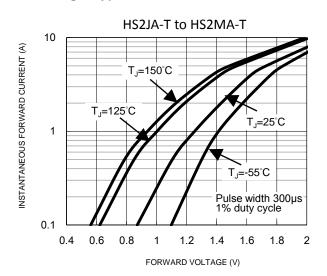
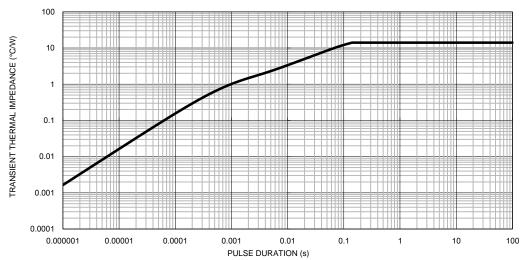


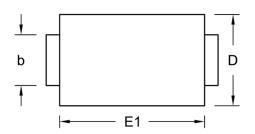
Fig.9 Typical Transient Thermal Impedance

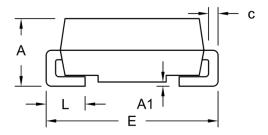




PACKAGE OUTLINE DIMENSIONS

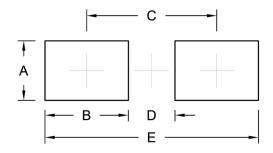
DO-214AC (SMA)





DIM.	Unit	(mm)	Unit (inch)		
Dilvi.	Min.	Max.	Min.	Max.	
Α	1.70	2.30	0.067	0.091	
A1	0.05	0.20	0.002	0.008	
b	1.20	1.80	0.047	0.071	
С	0.15	0.41	0.006	0.016	
D	2.40	3.00	0.094	0.118	
E	4.80	5.40	0.189	0.213	
E1	4.00	4.60	0.157	0.181	
L	0.75	1.60	0.030	0.063	

SUGGESTED PAD LAYOUT



Symbol	Unit (mm)	Unit (inch)
A	1.82	0.072
В	2.56	0.101
С	3.99	0.157
D	1.43	0.056
E	6.55	0.258

MARKING DIAGRAM



P/N = Marking Code G = Green Compound YW = Date Code

= Factory Code



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